

Listing of Claims

1. - 32. (canceled)

33. (currently amended) A semiconductor device comprising:

a semiconductor substrate;

a transistor formed on said semiconductor substrate;

an insulating film covering said semiconductor substrate and said transistor;

a contact plug buried in said insulating film and connected to a diffusion layer of said transistor; and

a ferroelectric capacitor formed on said insulating film and connected to said transistor by said contact plug,

said ferroelectric capacitor having a lower electrode, a ferroelectric film formed on said lower electrode, an upper electrode formed on and having an area smaller than said ferroelectric film, and a protective film formed in said self alignment with side walls of said upper electrode to cover the surface of said ferroelectric film.

34. - 47. (canceled)